



DMP3056L

30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Rds(on) max	I _{D MAX} T _A = +25°C
-30V	50mΩ @ V _{GS} =-10V	-4.3A
-30 V	70mΩ @ V _{GS} =-4.5V	-3.7A

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Features

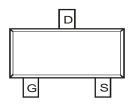
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

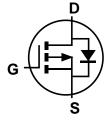
- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish Annealed over Alloy 42 Leadframe) (e3)
- Terminal Connections: See Diagram
- Weight: 0.009 grams (Approximate)



Top View



Top View Pin Configuration



Equivalent Circuit

Ordering Information (Note 4)

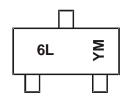
Part Number	Case	Packaging
DMP3056L-7	SOT23	3000/Tape & Reel
DMP3056L-13	SOT23	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

SOT23

Marking Information



6L = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Year	2012		~	2016		2017	2018		2019	2020		2021
Code	Z		~	D		Е	F		G	Н		I
Month	Jan	Feb	Mar	Apr	Mav	Jun	Jul	Aug	Sep	Oct	Nov	Dec
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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage	V _{GSS}	±25	V		
Drain Current (Note 5) V _{GS} = -10V	Steady State	I _D	-4.3 -3.4	А	
Pulsed Drain Current (Note 6)			I _{DM}	-20	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_{D}	1.38	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ hetaJA}$	91	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

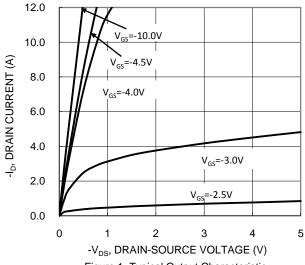
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

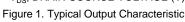
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_		V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_		-1	μΑ	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100 ±800	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$ $V_{GS} = \pm 25V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)	•	•		•		
Gate Threshold Voltage	V _{GS(TH)}	-1	_	-2.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance	R _{DS(ON)}		35 50	50 70	mΩ	$V_{GS} = -10V, I_D = -6.0A$ $V_{GS} = -4.5V, I_D = -5.0A$
Diode Forward Voltage	V _{SD}	_	_	-1.2	V	$V_{GS} = 0V, I_{S} = -1.7A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	_	642	_	pF	
Output Capacitance	Coss	_	65	_	pF	$V_{DS} = -25V$, $V_{GS} = 0V$, $f = 1.0MHz$
Reverse Transfer Capacitance	C _{rss}	_	48	_	pF	
Gate Resistance	R _G	_	15	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V _{GS} = -4.5V)	Q_{G}	_	5.8	_	nC	V _{DS} = -15V, I _D = -6A
Total Gate Charge (V _{GS} = -10V)	Q_{G}		11.8			
Gate-Source Charge	Q _{GS}		2.0		nC	$V_{DS} = -15V, I_{D} = -6A$
Gate-Drain Charge	Q_{GD}	_	2.4	_		
Turn-On Delay Time	t _{D(ON)}	_	4.9	_		
Rise Time	t _R	_	4.7	_	ne	$V_{DS} = -15V$, $V_{GS} = -10V$,
Turn-Off Delay Time	t _{D(OFF)}	_	35.2	_	ns	$I_D = -1A$, $R_G = 6.0\Omega$
Fall Time	t _F		18.2	_		

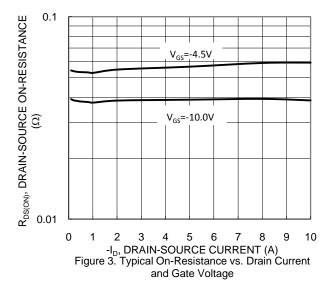
Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
- 6. Pulse width ≤10µS, Duty Cycle ≤1%.
- Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.









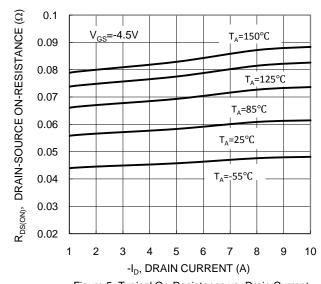


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

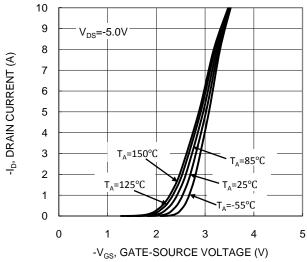


Figure 2. Typical Transfer Characteristic

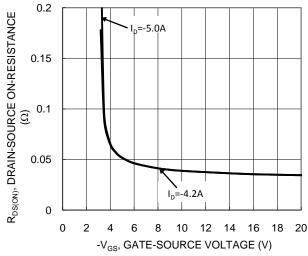


Figure 4. Typical Transfer Characteristic

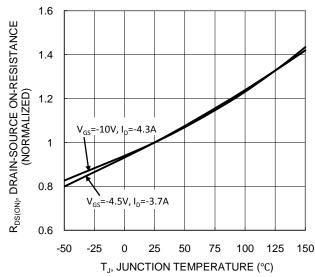
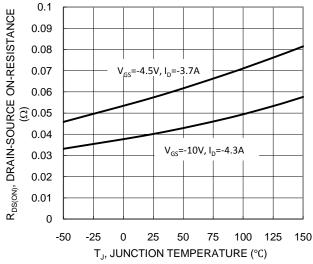


Figure 6. On-Resistance Variation with Temperature







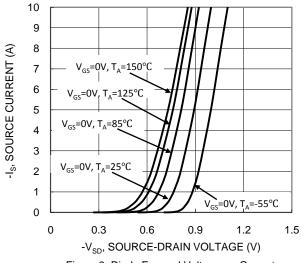
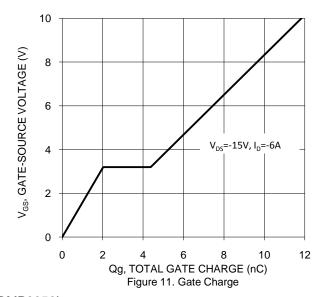


Figure 9. Diode Forward Voltage vs. Current



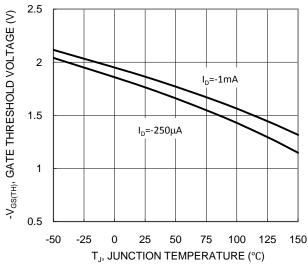


Figure 8. Gate Threshold Variation vs. Junction Temperature

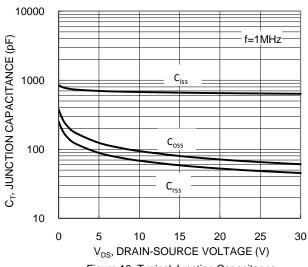
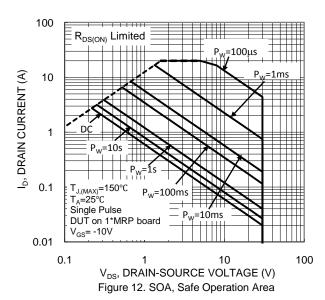
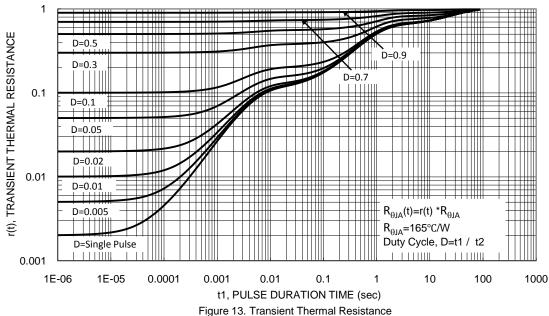


Figure 10. Typical Junction Capacitance



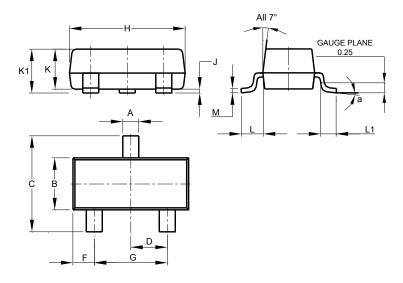




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



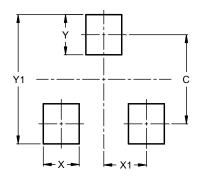
SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All Dimensions in mm								



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)				
С	2.0				
Х	0.8				
X1	1.35				
Υ	0.9				
Y1	2.9				

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